

2-pack-integrated intelligent Power System

#### SKiiP 2414 GB17E4-4DUL V2

#### Features\*

- · Intelligent Power Module
- Integrated current and temperature measurement
- Integrated DC-link measurement
- · Solder free power section
- IGBT4 and CAL4F technology
- Safety isolated switching and sensor signals
- · Digital signal transmission
- CAN Interface
- 100% tested IPM
- · RoHS compliant
- UL file no. E242581

#### **Typical Applications**

- · Renewable energies
- Traction
- Elevators
- · Industrial drives

#### Remarks

For further information please refer to SKiiP®4 Technical Explanation

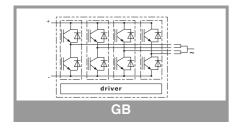
#### **Footnotes**

1)With assembly of suitable MKP capacitor per terminal

 $^{\dot{2})}$  The specified maximum operation junction temperature  $T_{\nu jop}$  can be > 150°C for a max. of 1000cum. Operations hours

Absolute Maximum Ratings							
Symbol	Conditions		Values	Unit			
System							
V <sub>CC</sub> 1)	Operating DC link	/oltage	1300	V			
V <sub>isol</sub>	DC, t = 1 s, each po	olarity	5600	V			
I <sub>t(RMS)</sub>	per AC terminal, rm	s, sinusoidal current	500	Α			
I <sub>max (peak)</sub>	max. peak current	of power section	3600	Α			
I <sub>FSM</sub>	$T_j = 175 {}^{\circ}\text{C},  t_p = 10$	ms, sin 180°	15885	Α			
l <sup>2</sup> t	$T_j = 175 {}^{\circ}\text{C},  t_p = 10$	ms, diode	1262	kA <sup>2</sup> s			
f <sub>out</sub>	fundamental output (sinusoidal)	t frequency	1	kHz			
T <sub>stg</sub>	storage temperatur	е	-40 85	°C			
IGBT							
$V_{CES}$	T <sub>j</sub> = 25 °C		1700	V			
Ic	T <sub>i</sub> = 175 °C	T <sub>s</sub> = 25 °C	3385	Α			
	1,-175 0	T <sub>s</sub> = 70 °C	2723	Α			
I <sub>Cnom</sub>			2400	Α			
T <sub>j</sub> <sup>2)</sup>	junction temperature		-40 175	°C			
Diode							
$V_{RRM}$	T <sub>j</sub> = 25 °C		1700	V			
l <sub>F</sub>	T <sub>j</sub> = 175 °C	T <sub>s</sub> = 25 °C	2362	Α			
		T <sub>s</sub> = 70 °C	1869	Α			
I <sub>Fnom</sub>			2400	Α			
T <sub>j</sub> <sup>2)</sup>	junction temperature		-40 175 °C				
Driver							
Vs	power supply		19.2 28.8	V			
$V_{iH}$	input signal voltage (high)		V <sub>s</sub> + 0.3	V			
dv/dt	secondary to primary side		75	kV/μs			
f <sub>sw</sub>	switching frequenc	y	10	kHz			

Characteristics								
Symbol	Conditions	min.	typ.	max.	Unit			
IGBT								
V <sub>CE(sat)</sub>	I <sub>C</sub> = 2400 A	T <sub>j</sub> = 25 °C		2.12	2.43	V		
	at terminal	T <sub>j</sub> = 150 °C		2.53	2.79	V		
$V_{CE0}$		T <sub>j</sub> = 25 °C		1.10	1.20	V		
		T <sub>j</sub> = 150 °C		1.00	1.10	V		
r <sub>CE</sub>	at terminal	T <sub>j</sub> = 25 °C		0.42	0.51	mΩ		
	at terriiriai	T <sub>j</sub> = 150 °C		0.64	0.70	mΩ		
E <sub>on</sub> + E <sub>off</sub>	I <sub>C</sub> = 2400 A	V <sub>CC</sub> = 900 V		1780		mJ		
	T <sub>j</sub> = 150 °C	V <sub>CC</sub> = 1300 V		2840		mJ		
R <sub>th(j-s)</sub>	per IGBT switch				0.0138	K/W		
R <sub>th(j-r)</sub>	per IGBT switch				0.008	K/W		





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#### Remarks

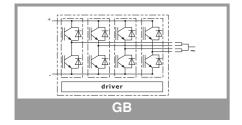
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#### **Footnotes**

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Characteristics								
Symbol	Conditions		min.	typ.	max.	Unit		
Diode			•					
$V_F = V_{EC}$	I <sub>F</sub> = 2400 A	T <sub>i</sub> = 25 °C		2.02	2.34	٧		
	at terminal $T_i = 150 ^{\circ}\text{C}$			2.27	2.62	V		
V <sub>F0</sub>		T <sub>j</sub> = 25 °C		1.21	1.36	V		
		T <sub>j</sub> = 150 °C		0.99	1.12	V		
r <sub>F</sub>	at tarminal	T <sub>j</sub> = 25 °C		0.34	0.41	mΩ		
	at terminal	T <sub>j</sub> = 150 °C		0.53	0.63	mΩ		
E <sub>rr</sub>	I <sub>F</sub> = 2400 A	V <sub>R</sub> = 900 V		412		mJ		
	T <sub>j</sub> = 150 °C	V <sub>R</sub> = 1300 V		664		mJ		
R <sub>th(j-s)</sub>	per diode switch				0.0281	K/W		
R <sub>th(j-r)</sub>	per diode switch				0.02	K/W		
Driver	l		I					
Vs	supply voltage non	stabilized	19.2	24	28.8	V		
I <sub>S0</sub>	bias current @V <sub>s</sub> = 2			260		mA		
Is	$k_1 = 46 \text{ mA/kHz}, k_2$ $f_{\text{out}} = 50 \text{Hz}, \text{ sinusoid}$	= 260	+ k <sub>1</sub> * f <sub>sw</sub>	+ k <sub>2</sub> * l <sub>AC</sub> <sup>2</sup>	mA			
$V_{IT+}$	input threshold volt	age (HIGH)	0,7*V <sub>s</sub>			V		
V <sub>IT-</sub>	input threshold volt	age (LOW)			0,3*V <sub>s</sub>	٧		
R <sub>IN</sub>	input resistance			13		kΩ		
C <sub>IN</sub>	input capacitance		1		nF			
t <sub>pRESET</sub>	error memory reset time			500		ms		
t <sub>pReset(OCP)</sub>	Over current reset time, FRT-function can be activated via CAN interface					μs		
t <sub>TD</sub>	top / bottom switch interlock time			3		μs		
t <sub>jitter</sub>	jitter clock time			50	58	ns		
t <sub>SIS</sub>	short pulse suppres	ssion time		0.6		μs		
t <sub>POR</sub>	Power-On-Reset co	ompleted			1	S		
l <sub>digiout</sub>	digital output sink o (HALT-signal)	urrent			16	mA		
V <sub>it+ HALT</sub>	input threshold volt (Low>High)	age HIGH HALT	0,6*V <sub>s</sub>			V		
V <sub>it-HALT</sub>	input threshold voltage LOW HALT (High> Low)				0.4*V <sub>s</sub>	V		
t <sub>d(err)</sub>	Error delay time (from detection to HALT), (depends on kind of error)		3		370	μs		
I <sub>TRIPSC</sub>	over current trip level		3600			A <sub>PEAK</sub>		
I <sub>LL</sub>				n.a.		A <sub>PEAK</sub>		
T <sub>trip</sub>	over temperature tr	128	135	142	°C			
T <sub>DriverTrip</sub>	over temperature P	CB trip level	113	120	124	°C		
$V_{DCtrip}$	over voltage trip lev deactivated via CA	1300	1340	1380	V			
V <sub>DCtripLL</sub>			n.a.		V			
· · ·						i		





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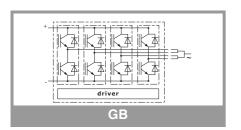
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Characteristics								
Symbol	Conditions	min.	typ.	max.	Unit			
System								
t <sub>d(on)IO</sub>	V <sub>CC</sub> = 1300 V I <sub>C</sub> = 2400 A	turn on propagation delay time		2.8		μѕ		
$t_{\text{d(off)IO}}$	$T_j = 25 ^{\circ}\text{C}$	turn off propagation delay time	2.6			μs		
$dV_{\text{CE}}/dt_{on}$	T 05 °C	I <sub>C</sub> = 0 A		14		kV/μs		
	$T_j = 25 ^{\circ}\text{C}$ $V_{CC} = 1300 ^{\circ}\text{V}$	$I_C = 2400 \text{ A}$		3		kV/μs		
$dV_{\text{CE}}\!/dt_{\text{off}}$		$I_C = 2400 \text{ A}$		10		kV/μs		
R <sub>th(s-a)</sub>	flow rate = 550 m <sup>3</sup> /h, T <sub>a</sub> =25°C, 500m above sea level				0.0225	K/W		
R <sub>CC'+EE'</sub>	measured per switch, T <sub>s</sub> = 25 °C			0.0675		mΩ		
L <sub>CE</sub>	commutation inductance			4.5		nΗ		
C <sub>CHC</sub>	coupling capacitance secondary to heat sink			6		nF		
C <sub>ps</sub>	coupling capacitance primary to secondary			0.08		nF		
I <sub>CES</sub> + I <sub>RD</sub>	$V_{GE} = 0 \text{ V}, V_{CE} = 1700 \text{ V}, T_j = 25 \text{ °C}$		0.199		mA			
M <sub>dc</sub>	DC terminals		6		8	Nm		
M <sub>ac</sub>	AC terminals		13		15	Nm		
W	SKiiP System w/o heat sink			3.22		kg		
Wh	heat sink		8		kg			

Isolation coordination acc. to EN 50178 and IEC 61800-5	5-1
Maximum grid RMS voltage, line-to-line, grounded delta mains	690V+20%
Installation altitude for maximum grid RMS voltage, line-to-line, grounded delta mains	2000m
Maximum grid RMS voltage, line-to-line, star point grounded mains	690V+20%
Installation altitude for maximum grid RMS voltage, line-to-line, star point grounded mains	4000m
Maximum transient peak voltage between low voltage circuit and mains	1900V
Pollution degree acc. to IEC 60664-1 outside the moulded power section	2
Overvoltage cat. acc. to IEC 60664-1 for mains	Ш
Overvoltage cat. acc. to UL 840 within mains	I
Overvoltage cat. acc. to UL 840 between mains and ground	Ш
Overvoltage cat. acc. to UL 840 between mains and low voltage circuit	Ш
Basic isolation	between heat sink and mains
Reinforced isolation	between low voltage circuit and mains
Protection level acc. to IEC 60529	IP00

## Environmental conditions acc. to IEC 60721

	Storage	Transportation	Operation stationary use at weather protected locations	Operating ground vehicle installations	Operating ship environment
Climatic conditions	1K2 <sub>(1)</sub>	2K2 <sub>(1)</sub>	3K3 <sub>(1)</sub>	5K1 <sub>(1)</sub>	6K1 <sub>(1)</sub>
Biological conditions	1B1	2B1	3B1	5B1	6B1
Chemically active substances (excluded: salt spray)	1C2	2C1	3C2	5C2	6C2
Mechanically active substances	181	281	381	581	6S1
Mechanical conditions	1M3	(4)	3M6 <sub>(2)</sub>	5M3 <sub>(3)</sub>	6M3
Contaminating fluids				5F1	

- (1) expanded temperature range: -40°C / +85°C. Please note: by operation near 85°C the life time of product is reduced.
- (2) 3M7 possible, but due to the mechanic load capacity of external components like DC-Link capacitors limited to 3M6
- (3) 5M3 without impact of foreign bodies, stones
- (4) no declaration due to customer-specific packing

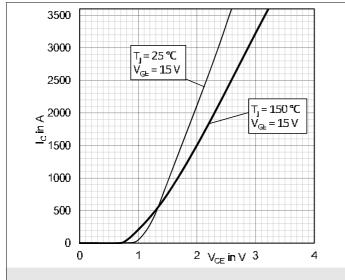


Fig. 1: Typical IGBT output characteristics

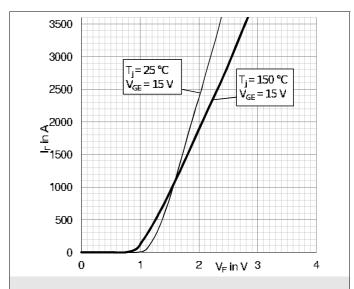


Fig. 2: Typical diode output characteristics

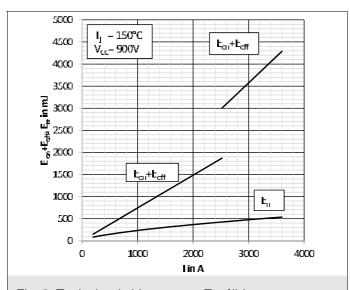


Fig. 3: Typical switching energy  $E = f(I_c)$ 

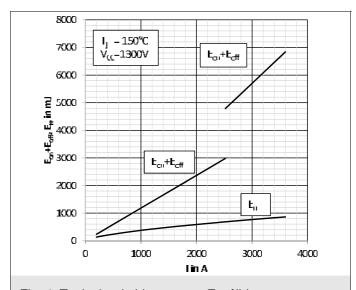


Fig. 4: Typical switching energy  $E = f(I_c)$ 

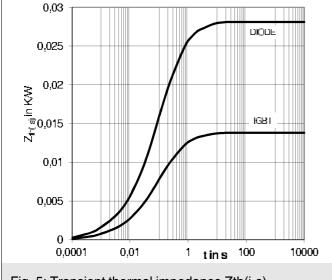


Fig. 5: Transient thermal impedance Zth(j-s)

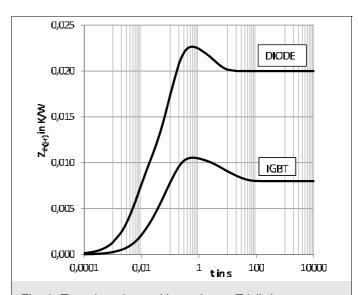


Fig. 6: Transient thermal impedance Zth(j-r)

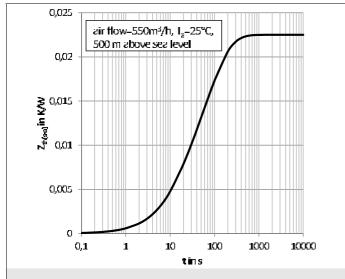


Fig. 7: Transient thermal impedance Zth(s-a)

	R <sub>th</sub> [K/W]					
	1	2	3	4	5	
$Z_{th(j-s)}$ I	0,0010	0,0049	0,0055	0,0017	0,0007	
$Z_{th(j-s)}$ D	0,0020	0,0100	0,0112	0,0034	0,0015	
$Z_{th(j-r)}$ I	0,0021	0,0029	0,0058	-0,0013	-0,0015	
$Z_{th(j-r)}$ D	0,0075	0,0060	0,0098	-0,0033	0,0000	
$Z_{th(s-a)}$	0,0012	0,0052	0,0123	0,0038	0,0000	
			tau [s]			
	1	2	3	4	5	
$Z_{th(j-s)}$ I	3,6500	0,4100	0,0650	0,0090	0,0008	
$Z_{th(j-s)}$ D	3,6500	0,4100	0,0650	0,0090	0,0008	
$Z_{th(j-r)}$ I	0,0130	0,0500	0,1200	4,4000	21,000	
$Z_{th(j-r)}$ D	0,0060	0,0650	0,1300	3,2500	1,0000	
$Z_{th(s-a)}$	9,000	18,900	73,000	161,000	1,0000	

Fig. 8: Coefficients of thermal impedances

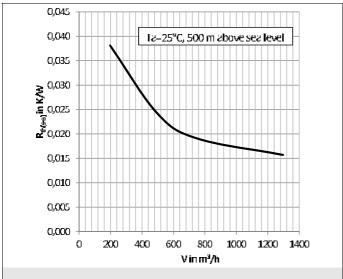


Fig. 9: Thermal resistance Rth(s-a) versus flow rate V

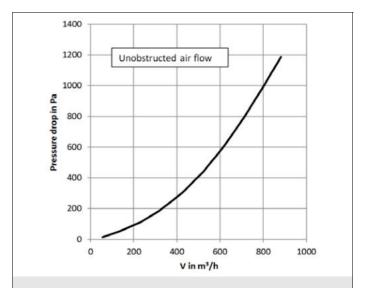
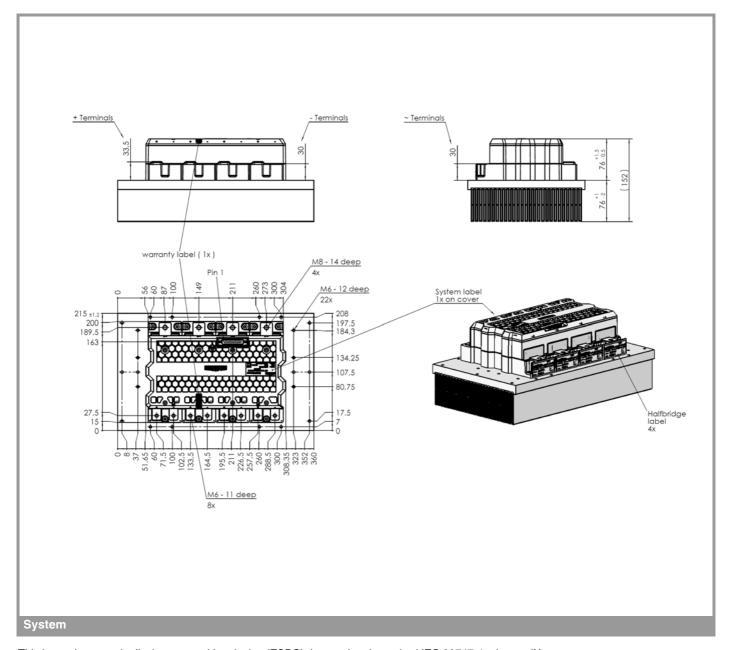


Fig. 10: Pressure drop  $\Delta p$  versus flow rate V



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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